

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI ULBM2SL is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.75 A
V_{CB0}	36 V
V_{CER}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	5.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	35.0 °C/W

PACKAGE STYLE .280 4L PILL

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 / 1.52
F	.118 / 3.00	.130 / 3.30

ORDER CODE: ASI10678

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 25 mA	16			V
BV_{CES}	I _C = 5 mA	36			V
BV_{EBO}	I _E = 1 mA	4.0			V
I_{CB0}	V _{CB} = 15 V			1.0	mA
I_{CER}	V _{CE} = 10 V R _{BE} = 80 Ω			0.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	40		200	---
C_{ob}	V _{CB} = 7.5 V f = 1.0 MHz			10	pF
P_G η_C	V _{CC} = 12.5 V P _{OUT} = 2.0 W f = 470 MHz	11.5	60		dB %